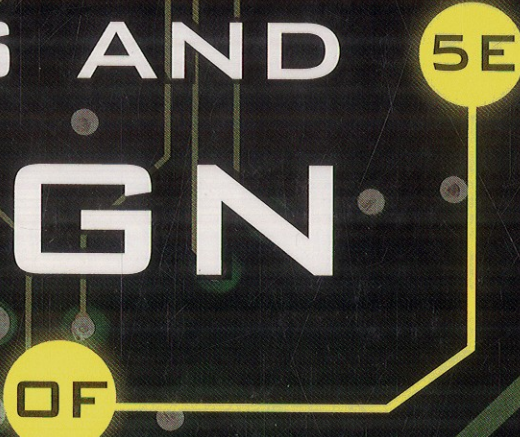


GRAY • HURST • LEWIS • MEYER

ANALYSIS AND
D E S I G N
OF
ANALOG
INTEGRATED
CIRCUITS



5E

OF

INTERNATIONAL STUDENT VERSION

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